

60V N-Channel Enhancement Mode MOSFET

Voltage 60 V Current

33 A

Features

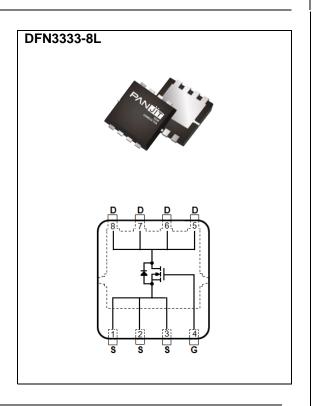
- R_{DS(ON)}, V_{GS}@10V, I_D@15A<21mΩ
- R_{DS(ON)}, V_{GS}@4.5V, I_D@8A<24mΩ
- High switching speed
- Improved dv/dt capability
- Low reverse transfer capacitance
- AEC-Q101 qualified
- Lead free in compliance with EU RoHS 2.0
- Green molding compound as per IEC 61249 standard

Mechanical Data

• Case: DFN3333-8L Package

• Terminals : Solderable per MIL-STD-750, Method 2026

• Approx. Weight: 0.03 grams



Maximum Ratings and Thermal Characteristics (T_A=25°C unless otherwise noted)

PARAMETER		SYMBOL	LIMIT	UNITS	
Drain-Source Voltage		V _{DS}	60	.,,	
Gate-Source Voltage		V _{GS}	<u>+</u> 20	V	
Continuous Drain Current(Note 4)	Tc=25°C	I _D	33		
	T _C =100°C		21	Α	
Pulsed Drain Current(Note 1)	Tc=25°C	I _{DM}	132		
Power Dissipation	T _C =25°C	Po	53	10/	
	Tc=100°C		26	W	
Continuous Drain Current(Note 4)	T _A =25°C	lο	6		
	T _A =70°C		5	Α	
Power Dissipation	T _A =25°C	Po	2.4	W	
	T _A =70°C		1.6		
Single Pulse Avalanche Energy ^(Note 6)		Eas	42	mJ	
Operating Junction and Storage Temperature Range		T _J ,T _{STG}	-55~175	°C	
Typical Thermal Resistance ^(Note 4,5)	Junction to Case	R ₀ JC	2.8	°C/W	
	Junction to Ambient	R _{θJA}	62.5		

• Limited only By Maximum Junction Temperature



Electrical Characteristics (T_A=25°C unless otherwise noted)

PARAMETER	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNITS	
Static			_		_		
Drain-Source Breakdown Voltage	BV _{DSS} V _{GS} =0V, I _D =250uA		60	-	-	- v	
Gate Threshold Voltage	V _{GS(th)}	V _{DS} =V _{GS} , I _D =250uA	1	1.73	2.5	V	
Drain-Source On-State Resistance	R _{DS(on)}	V _{GS} =10V, I _D =15A	-	18	21	mΩ	
		V _{GS} =4.5V, I _D =8A	-	21	24		
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} =60V, V _{GS} =0V	-	-	1	uA	
Gate-Source Leakage Current	Igss	V _{GS} = <u>+</u> 20V, V _{DS} =0V	-	-	<u>+</u> 100	nA	
Dynamic ^(Note 7)							
Total Gate Charge	Q_g	\/ 00\/ L 45A	-	28	-	nC	
Gate-Source Charge	Q_gs	V _{DS} =30V, I _D =15A, V _{GS} =10V ^(Note 1,2)	-	3.5	-		
Gate-Drain Charge	Q_{gd}	VGS=10V(************************************	-	6.5	-		
Input Capacitance	Ciss	\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\\	-	1680	-	pF	
Output Capacitance	Coss	V _{DS} =20V, V _{GS} =0V,	-	115	-		
Reverse Transfer Capacitance	Crss	f=1MHZ	-	85	-		
Turn-On Delay Time	td _(on)	.,	-	7.2	-		
Turn-On Rise Time	t _r	V_{DD} =30V, I_{D} =1A, V_{GS} =10V, R_{G} =6 Ω	-	38	-	ns	
Turn-Off Delay Time	td _(off)		-	34	-		
Turn-Off Fall Time	t _f	(1000 1,2)	-	8.2	-		
Drain-Source Diode							
Maximum Continuous Drain-Source			-	-	33	А	
Diode Forward Current	Is						
Reverse Recovery Time	V _{SD}	I _S =1A, V _{GS} =0V	-	0.68	1	V	

NOTES:

- 1. Pulse width<300us, Duty cycle<2%.
- 2. Essentially independent of operating temperature typical characteristics.
- 3. Repetitive rating, pulse width limited by junction temperature $T_{J(MAX)}$ =150°C. Ratings are based on low frequency and duty cycles to keep initial T_J =25°C.
- 4. The maximum current rating is package limited.
- 5. R_{OJA} is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. Mounted on a 1 inch² with 2oz.square pad of copper.
- 6. The test condition is L=0.1mH, I_{AS}=29A, V_{DD}=25V, V_{GS}=10V, Starting T_J=25°C.
- 7. Guaranteed by design, not subject to production testing.



TYPICAL CHARACTERISTIC CURVES

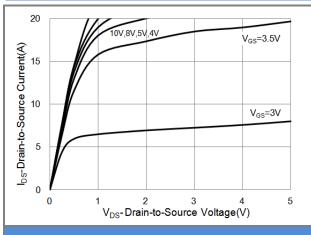


Fig.1 On-Region Characteristics

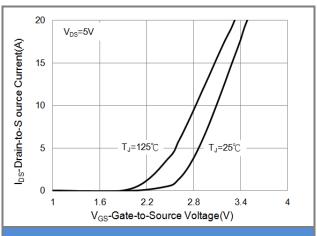


Fig.2 Transfer Characteristics

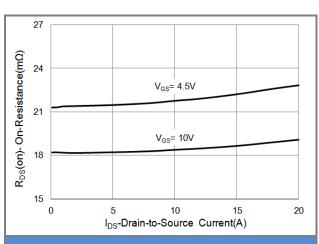


Fig.3 On-Resistance vs. Drain Current

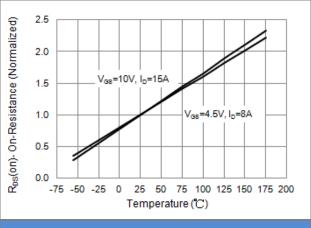
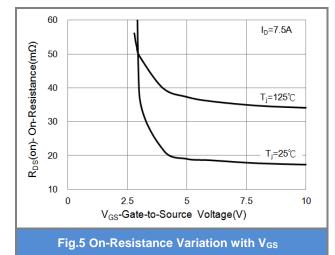


Fig.4 On-Resistance vs. Junction temperature



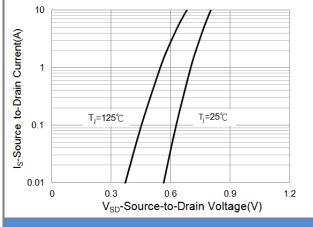


Fig.6 Source-Drain Diode Forward Voltage



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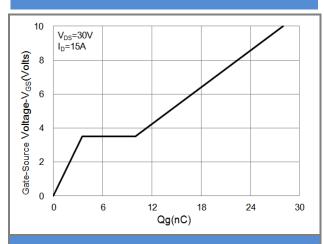


Fig.7 Gate-Charge Characteristics

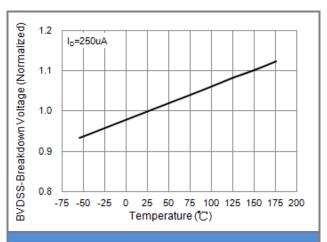


Fig.8 Breakdown Voltage Variation vs. Temperature

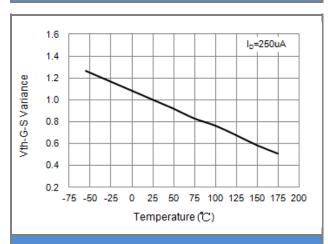


Fig.9 Threshold Voltage Variation with Temperature

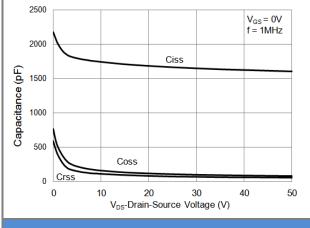
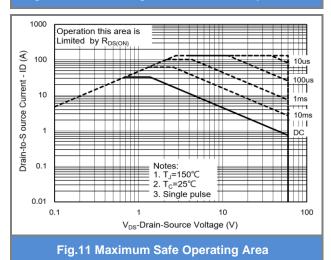


Fig.10 Capacitance vs. Drain-Source Voltage





TYPICAL CHARACTERISTIC CURVES

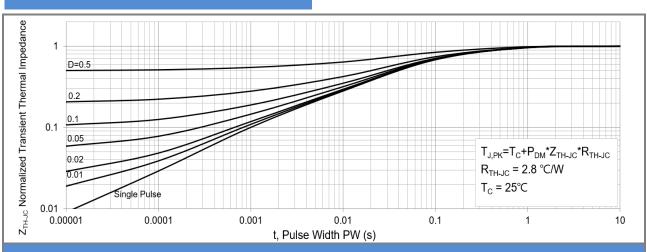


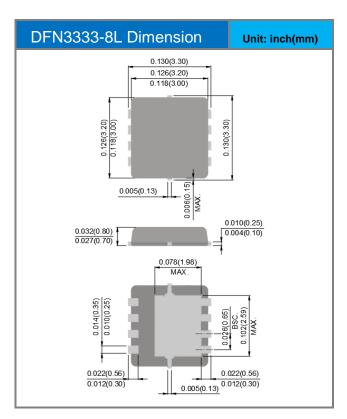
Fig.12 Normalized Transient Thermal Impedance vs. Pulse Width

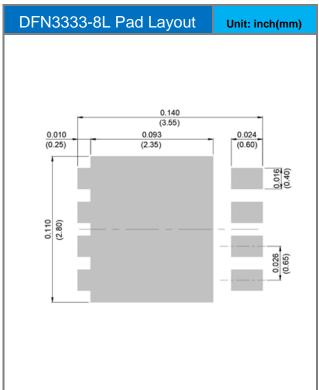


Part No. Packing Code Version

Part No. Packing Code	Package Type	Packing Type	Marking	Version
PJQ4466AP-AU_R2_000A1	DFN3333-8L	5K pcs / 13" reel	4466	Halogen free RoHS compliant

Packaging Information & Mounting Pad Layout







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